



60V P-Channel MOSFETS LDN6911S

SOT-23-3S Pin Configuration

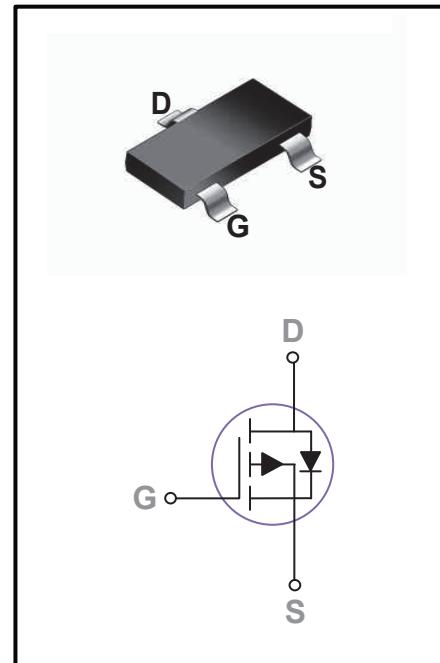
BVDSS	RDS(ON)	ID
-60V	190mΩ	-2A

Feature

- -60V, -2A, RDS(ON) = 190mΩ@VGS = -10V
- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

- Motor Drive
- Power Tools
- LED Lighting



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-60	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current – Continuous (T _C =25°C)	-2	A
	Drain Current – Continuous (T _C =100°C)	-1.25	A
I _{DM}	Drain Current – Pulsed ¹	-8	A
P _D	Power Dissipation (T _C =25°C)	1.56	W
	Power Dissipation – Derate above 25°C	0.012	W/°C
T _{STG}	Storage Temperature Range	-50 to 150	°C
T _J	Operating Junction Temperature Range	-50 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction to ambient	---	80	°C/W

MOSFET ELECTRICAL CHARACTERISTICS $T_A = 25^\circ C$ unless otherwise specified

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to $25^\circ C, I_D=-1mA$	---	-0.05	---	$V/\text{ }^\circ C$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-60V, V_{GS}=0V, T_J=25^\circ C$	---	---	-1	μA
		$V_{DS}=-48V, V_{GS}=0V, T_J=125^\circ C$	---	---	-10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V, I_D=-2A$	---	160	190	$m\Omega$
		$V_{GS}=-4.5V, I_D=-1.5A$	---	200	240	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2	-1.9	-2.5	V
			---	5	---	$mV/\text{ }^\circ C$
g_{fs}	Forward Transconductance	$V_{DS}=-10V, I_D=-2A$	---	3.5	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge ^{2,3}	$V_{DS}=-30V, V_{GS}=-10V, I_D=-2A$	---	8.2	12	nC
Q_{gs}	Gate-Source Charge ^{2,3}		---	1.8	3.6	
Q_{gd}	Gate-Drain Charge ^{2,3}		---	1.5	3	
$T_{d(on)}$	Turn-On Delay Time ^{2,3}	$V_{DD}=-30V, V_{GS}=-10V, R_G=6\Omega$	---	5.2	10	ns
T_r	Rise Time ^{2,3}		---	19	36	
$T_{d(off)}$	Turn-Off Delay Time ^{2,3}		---	35	67	
T_f	Fall Time ^{2,3}		---	10.6	20	
C_{iss}	Input Capacitance	$V_{DS}=-30V, V_{GS}=0V, F=1MHz$	---	425	615	pF
C_{oss}	Output Capacitance		---	35	50	
C_{rss}	Reverse Transfer Capacitance		---	20	30	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_s	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	-2	A
I_{SM}	Pulsed Source Current		---	---	-4	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=-1A, T_J=25^\circ C$	---	---	-1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

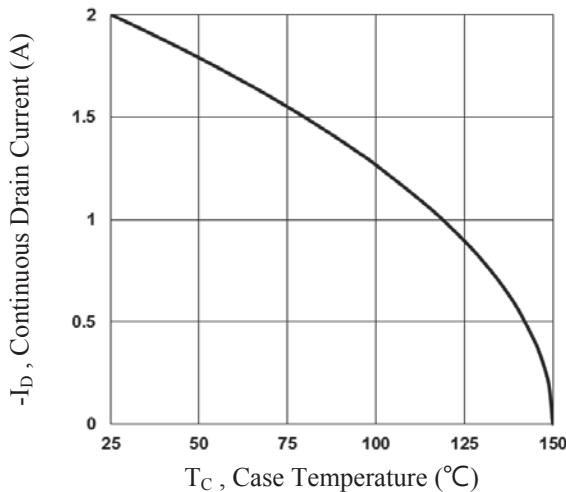


Fig.1 Continuous Drain Current vs. T_c

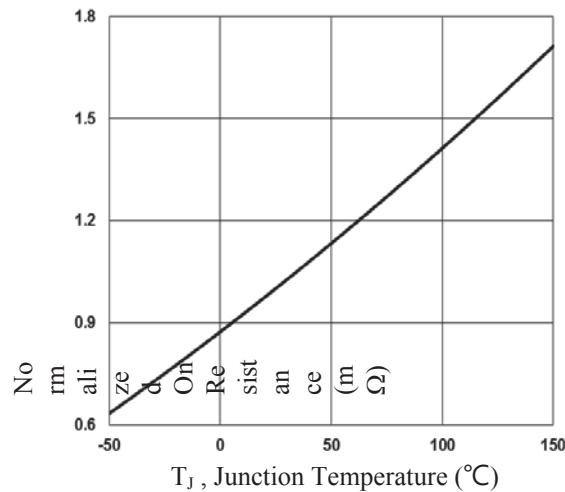


Fig.2 Normalized RDSON vs. T_j

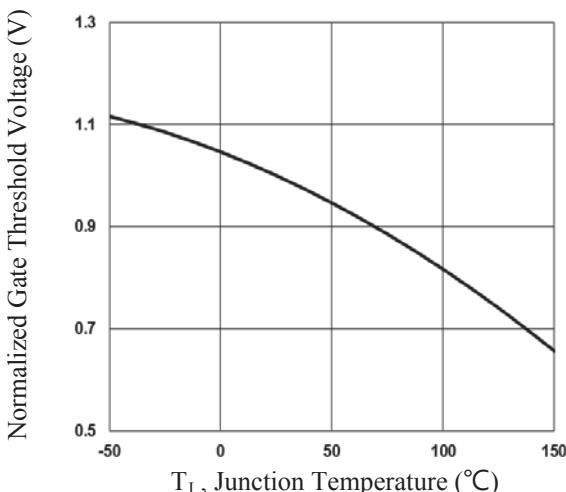


Fig.3 Normalized V_{th} vs. T_j

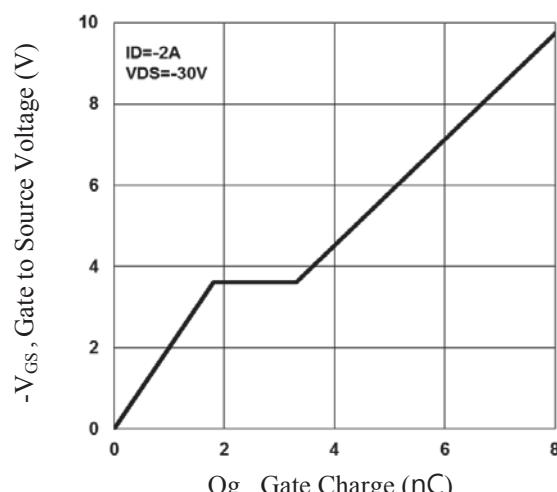


Fig.4 Gate Charge Waveform

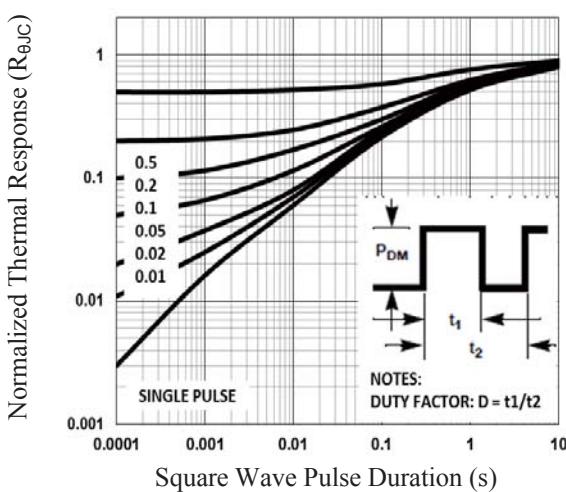


Fig.5 Normalized Transient Impedance

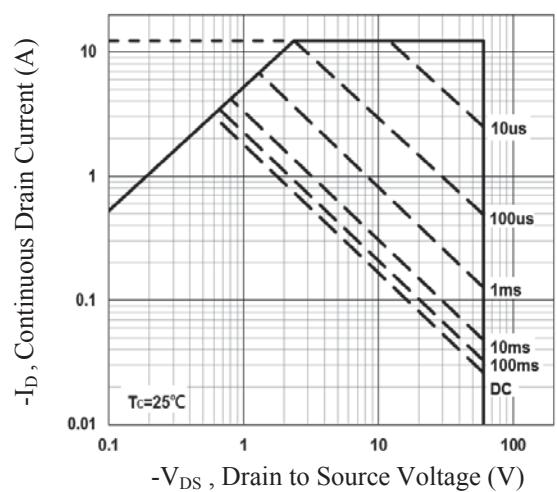


Fig.6 Maximum Safe Operation Area

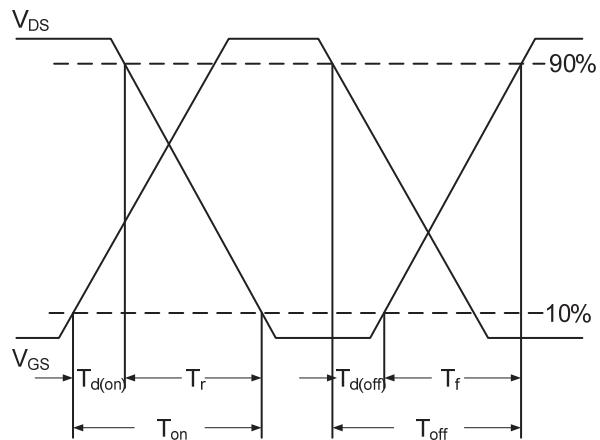


Fig.7 Switching Time Waveform

$$EAS = \frac{1}{2} L \times (-I_{AS})^2 \times \frac{-BV_{DSS}}{-BV_{DSS} - (-V_{DD})}$$

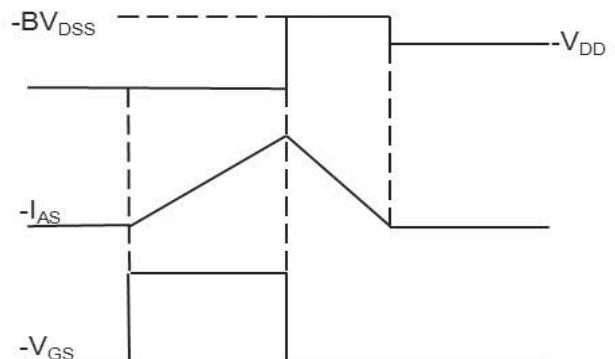
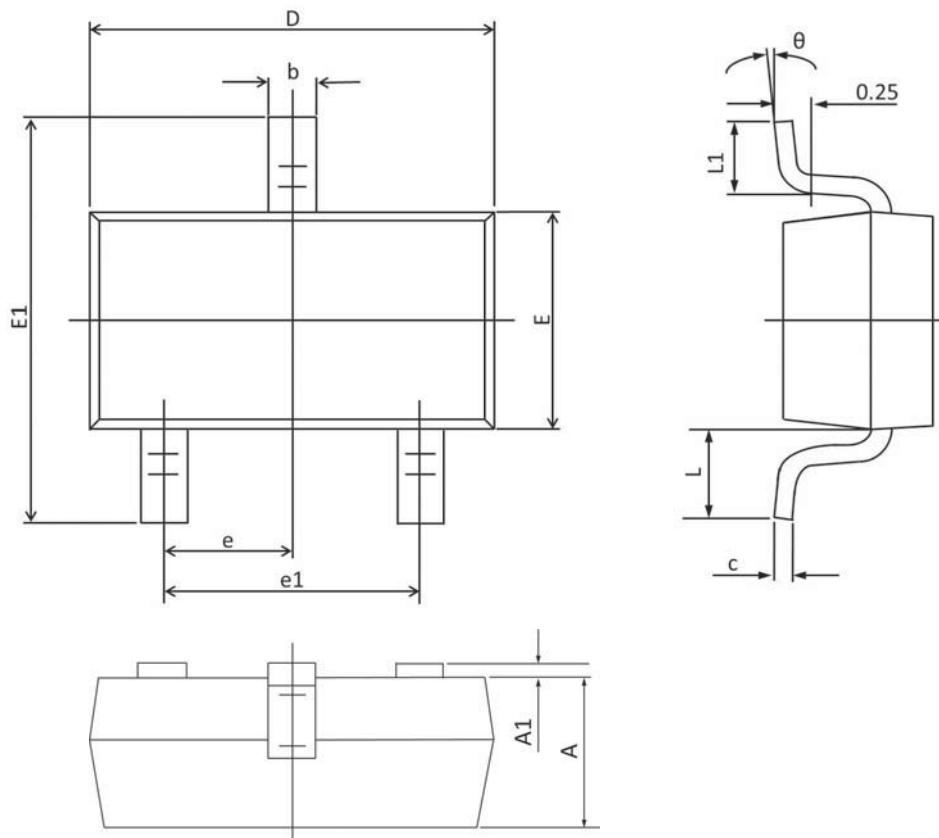


Fig.8 EAS Waveform

SOT23-3S PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.000	0.035	0.039
A1	0.000	0.100	0.000	0.004
b	0.300	0.500	0.012	0.020
c	0.090	0.110	0.003	0.004
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	1°	7°	1°	7°